



AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF THE CLAIMS:

Claims 1-29 (Cancelled)

30. (Currently Amended) A manufacture method for a nonvolatile semiconductor memory device ~~according to claim 29,~~ comprising:

a step of forming a well of a first conductivity type in a semiconductor substrate;

a step of forming a pair of semiconductor regions of a second conductivity type in the well of the first conductivity type, the pair of semiconductor regions being used as a source and a drain;

a step of forming a first gate on the semiconductor substrate via a first gate insulator;

a step of forming a second gate on a second insulator film covering the first gate; and

a step of forming a third gate via the second insulator film relative to the first gate and via a third insulator film relative to the semiconductor substrate,

wherein an impurity doped region of the first

conductivity type having an impurity concentration higher
than the well is formed in a channel region between the pair
of semiconductor regions, the impurity doped region being
not in contact with the semiconductor regions, and
_____ wherein the semiconductor regions and the impurity
region are formed in a self-alignment manner by tilted ion
implantation tilted in opposite directions from a normal of
the semiconductor substrate, by using one of the first to
third gates as a mask.

31. (Currently Amended) A manufacture method for a
nonvolatile semiconductor memory device according to claim
2930, wherein the gate used as a mask for forming the
impurity region through tilted ion implantation is one of a
single layer film of polysilicon, a stacked film of a
polysilicon film and a silicon oxide film, a stacked film of
a polysilicon film and a silicon nitride film, and a stacked
film of a polysilicon film, a silicon oxide film and a
silicon nitride film.

Claims 32-43 (Cancelled)

44. (Currently Amended) A manufacture method for a nonvolatile semiconductor memory device according to claim 2930, wherein the first conductivity type is a p-type and the second conductivity type is an n-type.

45. (Currently Amended) A manufacture method for a nonvolatile semiconductor memory device according to claim 2930, wherein the first conductivity type is an n-type and the second conductivity type is a p-type.

46. (Original) A manufacture method for a nonvolatile semiconductor memory device according to claim 44, wherein p-type impurities are boron or boron fluoride ions and n-type impurities are arsenic ions.

47. (Original) A manufacture method for a nonvolatile semiconductor memory device according to claim 45, wherein n-type impurities are phosphorous ions and p-type impurities are boron or boron fluoride ions.